

Amendments to the Specification

Please replace paragraph [0052] with the following rewritten paragraph:

[0052] As shown in Fig. 25, an eighth mask 208 is formed over the field oxide layer 180 the polysilicon gates 184. Using the eighth mask 208, a P+ source/drain 158 is ion implanted in the P-body 154 of the DMOS transistor 150 and a P+ source/drain 148 is ion implanted in the low voltage n-well ~~144~~142 of the CMOS transistor 140. Then, as shown in Fig. 26, the eighth mask 208 is removed.